

ALUMINUM NITRIDE FILMS AS AN EFFECTIVE THERMO-INTERFACE FOR POWERFUL SEMICONDUCTOR DEVICES

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Abstract

Highly efficient thermal interface materials (TIM) have been created using thin films of aluminum nitride (AlN) and were studied with the aim to remove heat from high-power light emitting diodes (LEDs). The experimental results for comparative tests of our, AlN-based TIM and industrial TIM in high-power (3 W) LED assemblies are presented.

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